

MJE18006G

Switch-mode

NPN Bipolar Power Transistor For Switching Power Supply Applications

The MJE18006G has an applications specific state-of-the-art die designed for use in 220 V line-operated switch-mode power supplies and electronic light ballasts.

Features

- Improved Efficiency Due to Low Base Drive Requirements:
 - ◆ High and Flat DC Current Gain h_{FE}
 - ◆ Fast Switching
 - ◆ No Coil Required in Base Circuit for Turn-Off (No Current Tail)
- Tight Parametric Distributions are Consistent Lot-to-Lot
- Standard TO-220
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V_{CEO}	450	Vdc
Collector-Emitter Breakdown Voltage	V_{CES}	1000	Vdc
Emitter-Base Voltage	V_{EBO}	9.0	Vdc
Collector Current – Continuous	I_C	6.0	Adc
– Peak (Note 1)	I_{CM}	15	
Base Current – Continuous	I_B	4.0	Adc
– Peak (Note 1)	I_{BM}	8.0	
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	100 0.8	W W/ $^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.25	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

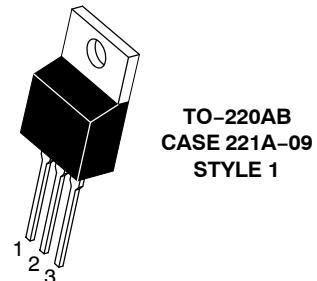
1. Pulse Test: Pulse Width = 5 ms, Duty Cycle $\leq 10\%$.



ON Semiconductor®

<http://onsemi.com>

POWER TRANSISTOR 6.0 AMPERES 1000 VOLTS – 100 WATTS



MARKING DIAGRAM



A = Assembly Location

Y = Year

WW = Work Week

G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE18006G	TO-220 (Pb-Free)	50 Units / Rail

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERMM/D.

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 100 \text{ mA}$, $L = 25 \text{ mH}$)	$V_{CEO(\text{sus})}$	450	—	—	Vdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $I_B = 0$)	I_{CEO}	—	—	100	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{EB} = 0$) ($T_C = 125^\circ\text{C}$) ($V_{CE} = 800 \text{ V}$, $V_{EB} = 0$)	I_{CES}	— — —	— 500 100	100	μAdc
Emitter Cutoff Current ($V_{EB} = 9.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	100	μAdc

ON CHARACTERISTICS

Base-Emitter Saturation Voltage ($I_C = 1.3 \text{ Adc}$, $I_B = 0.13 \text{ Adc}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 0.6 \text{ Adc}$)	$V_{BE(\text{sat})}$	— —	0.83 0.94	1.2 1.3	Vdc
Collector-Emitter Saturation Voltage ($I_C = 1.3 \text{ Adc}$, $I_B = 0.13 \text{ Adc}$) ($T_C = 125^\circ\text{C}$) ($I_C = 3.0 \text{ Adc}$, $I_B = 0.6 \text{ Adc}$) ($T_C = 125^\circ\text{C}$)	$V_{CE(\text{sat})}$	— — — —	0.25 0.27 0.35 0.4	0.6 0.65 0.7 0.8	Vdc
DC Current Gain ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($T_C = 125^\circ\text{C}$) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($T_C = 125^\circ\text{C}$) ($I_C = 1.3 \text{ Adc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($T_C = 25 \text{ to } 125^\circ\text{C}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	14 — 6.0 5.0 11 10	— 32 10 8.0 17 22	34 — — — — —	—

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ($I_C = 0.5 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	f_T	—	14	—	MHz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	75	120	pF
Input Capacitance ($V_{EB} = 8.0 \text{ V}$)	C_{ib}	—	1000	1500	pF
Dynamic Saturation Voltage: Determined 1.0 μs and 3.0 μs respectively after rising I_{B1} reaches 90% of final I_{B1} (see Figure 18)	$V_{CE(\text{dsat})}$	— — — — — — — —	5.5 12 3.0 7.0 9.5 14.5 2.0 7.5	— — — — — — — —	V

SWITCHING CHARACTERISTICS: Resistive Load (D.C. $\leq 10\%$, Pulse Width = 20 μs)

Turn-On Time	$(I_C = 3.0 \text{ Adc}$, $I_{B1} = 0.6 \text{ Adc}$, $I_{B2} = 1.5 \text{ Adc}$, $V_{CC} = 300 \text{ V}$)	t_{on}	— —	90 100	180 —	ns
Turn-Off Time		t_{off}	— —	1.7 2.1	2.5 —	μs
Turn-On Time	$(I_C = 1.3 \text{ Adc}$, $I_{B1} = 0.13 \text{ Adc}$, $I_{B2} = 0.65 \text{ Adc}$, $V_{CC} = 300 \text{ V}$)	t_{on}	— —	200 130	300 —	ns
Turn-Off Time		t_{off}	— —	1.2 1.5	2.5 —	μs

SWITCHING CHARACTERISTICS: Inductive Load ($V_{\text{clamp}} = 300 \text{ V}$, $V_{CC} = 15 \text{ V}$, $L = 200 \mu\text{H}$)

Fall Time	$(I_C = 1.5 \text{ Adc}$, $I_{B1} = 0.13 \text{ Adc}$, $I_{B2} = 0.65 \text{ Adc}$)	t_{fi}	— —	100 120	180 —	ns
Storage Time		t_{si}	— —	1.5 1.9	2.5 —	μs
Crossover Time		t_c	— —	220 230	350 —	ns
Fall Time	$(I_C = 3.0 \text{ Adc}$, $I_{B1} = 0.6 \text{ Adc}$, $I_{B2} = 1.5 \text{ Adc}$)	t_{fi}	— —	85 120	150 —	ns
Storage Time		t_{si}	— —	2.15 2.75	3.2 —	μs
Crossover Time		t_c	— —	200 310	300 —	ns

2. Proper strike and creepage distance must be provided.

TYPICAL STATIC CHARACTERISTICS

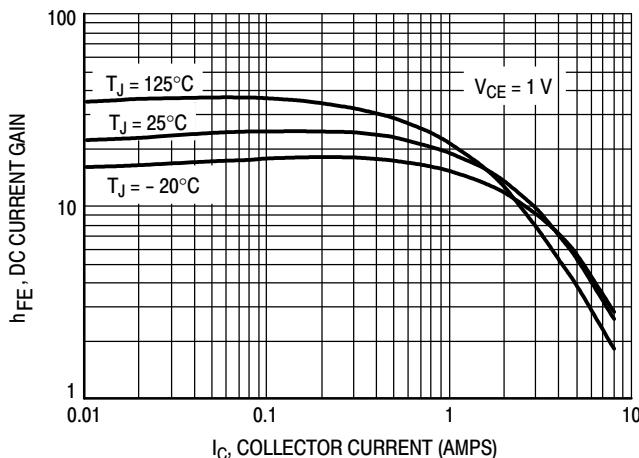


Figure 1. DC Current Gain @ 1 Volt

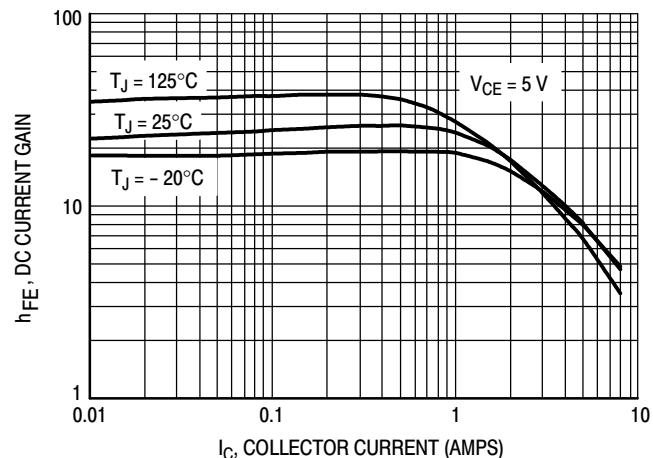


Figure 2. DC Current Gain @ 5 Volts

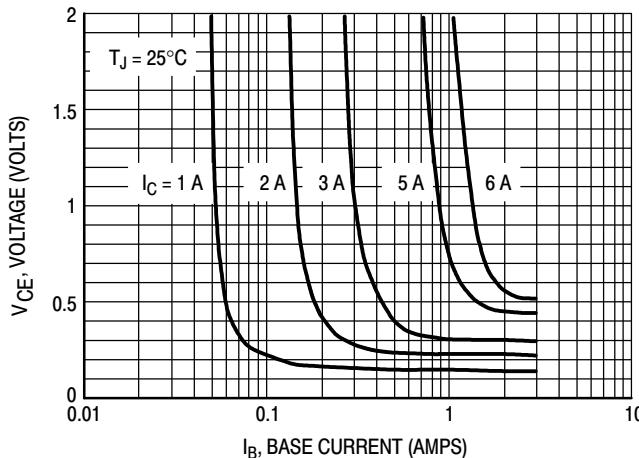


Figure 3. Collector Saturation Region

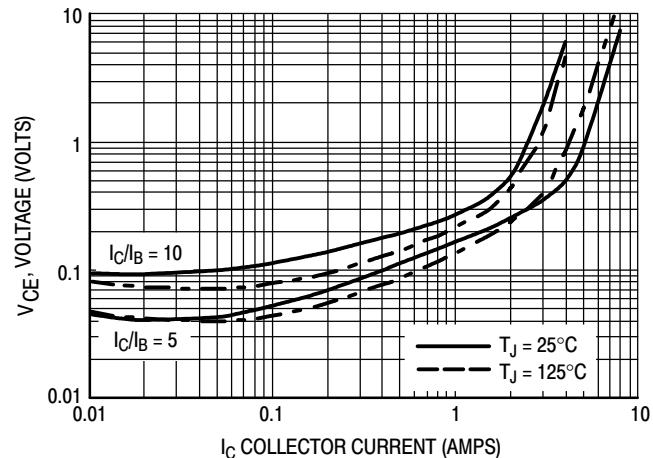


Figure 4. Collector-Emitter Saturation Voltage

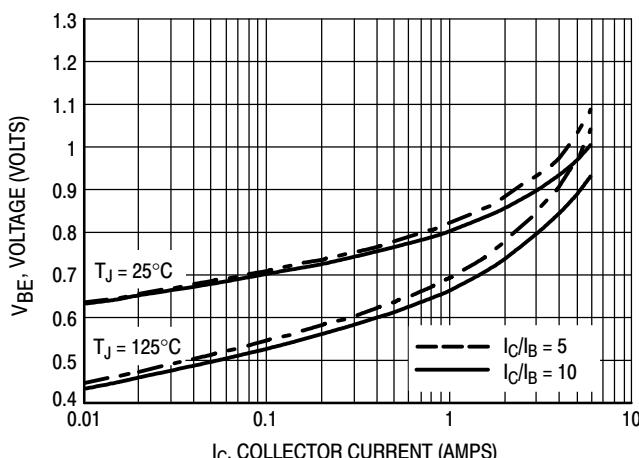


Figure 5. Base-Emitter Saturation Region

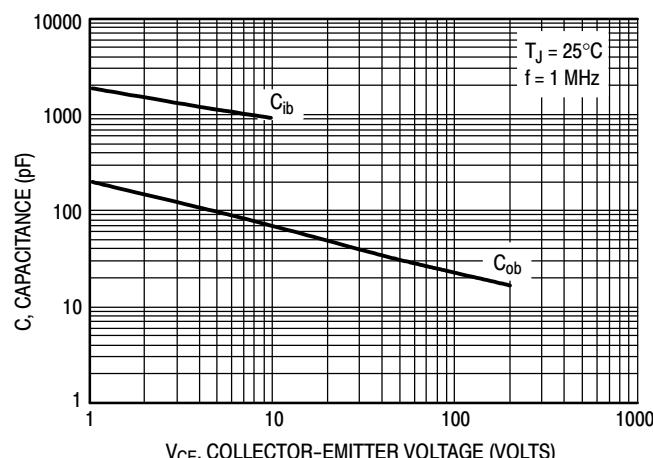


Figure 6. Capacitance

TYPICAL SWITCHING CHARACTERISTICS
($I_{B2} = I_C/2$ for all switching)

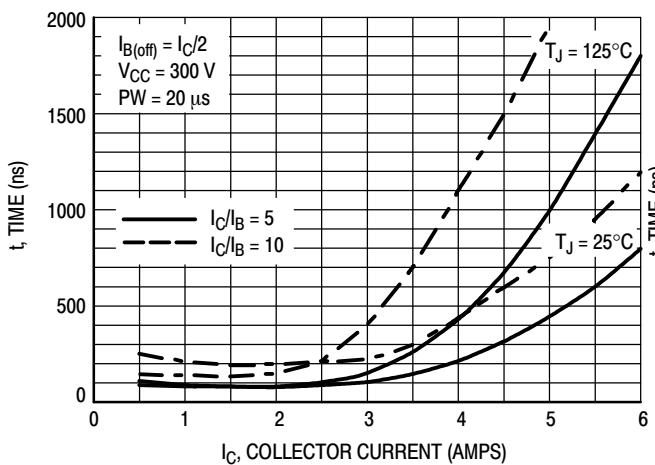


Figure 7. Resistive Switching, t_{on}

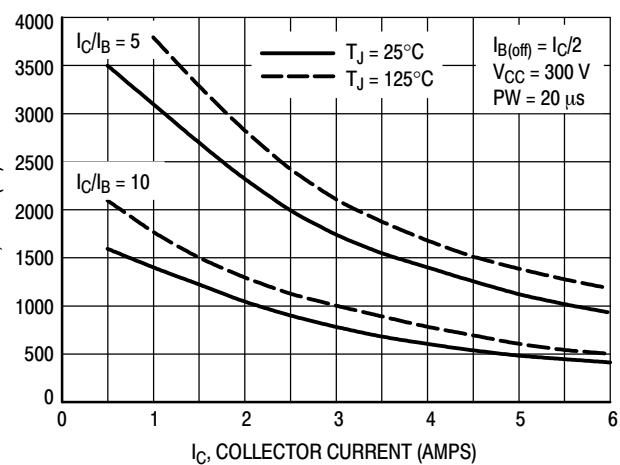


Figure 8. Resistive Switching, t_{off}

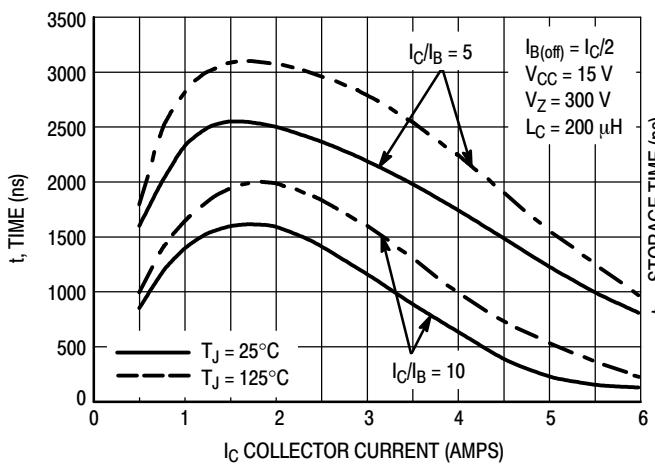


Figure 9. Inductive Storage Time, t_{si}

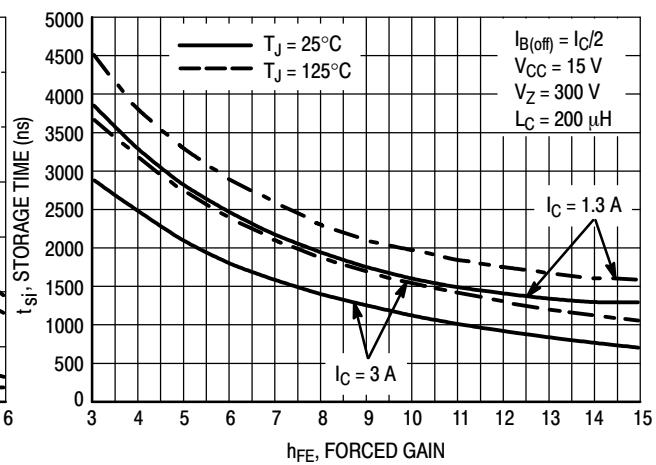


Figure 10. Inductive Storage Time, $t_{si}(h_{FE})$

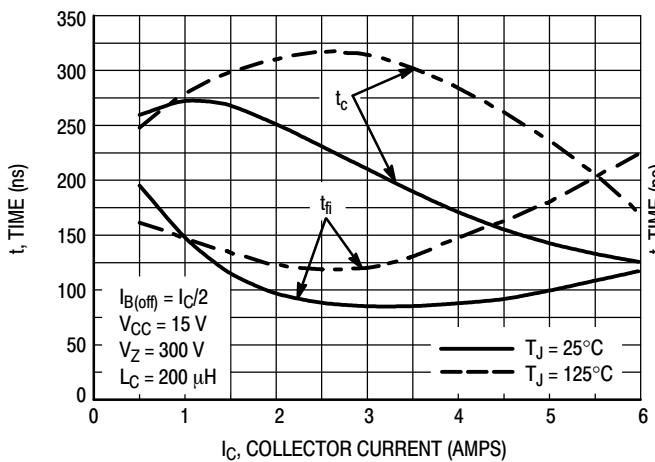


Figure 11. Inductive Switching, t_c and t_{fi}
 $I_C/I_B = 5$

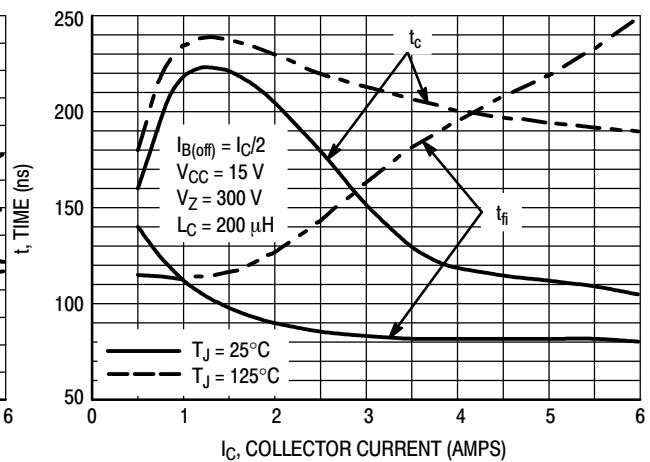


Figure 12. Inductive Switching, t_c and t_{fi}
 $I_C/I_B = 10$

TYPICAL SWITCHING CHARACTERISTICS
($I_{B2} = I_C/2$ for all switching)

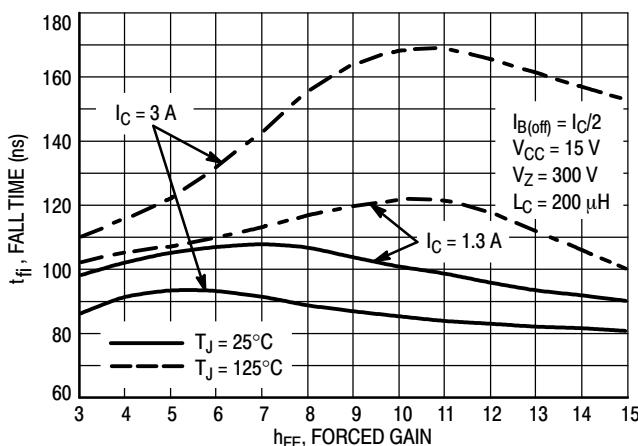


Figure 13. Inductive Fall Time

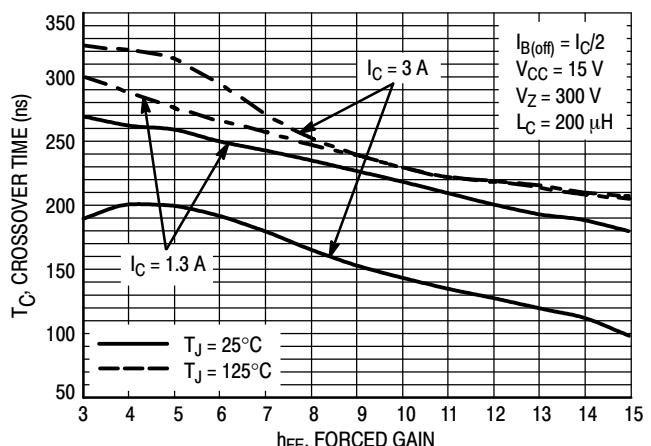


Figure 14. Inductive Crossover Time

GUARANTEED SAFE OPERATING AREA INFORMATION

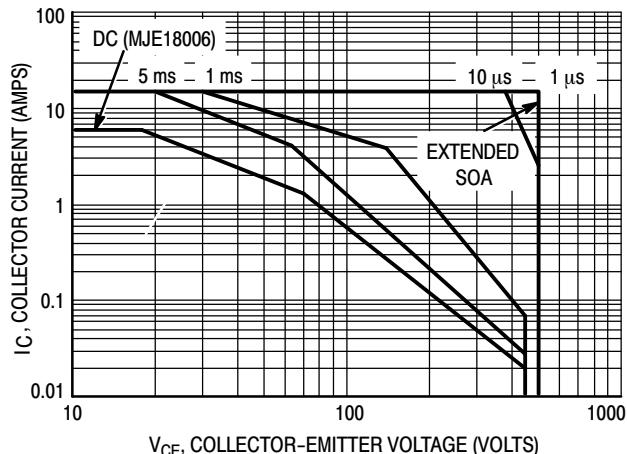


Figure 15. Forward Bias Safe Operating Area

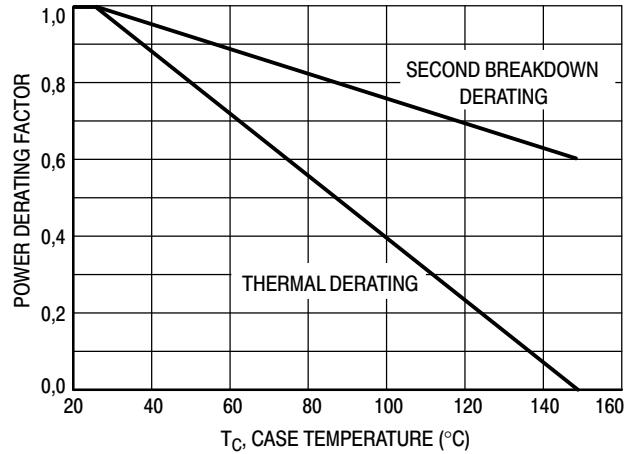


Figure 17. Forward Bias Power Derating

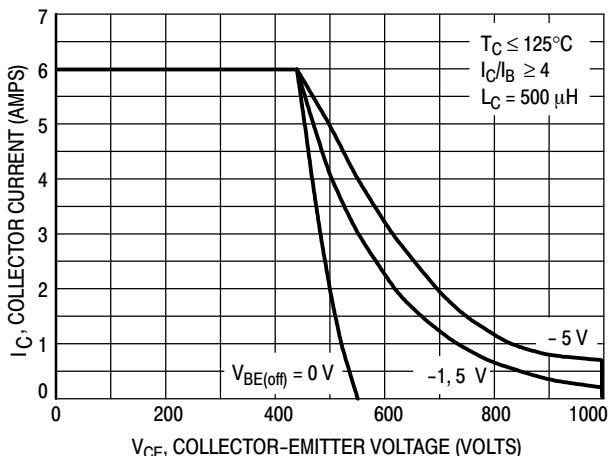


Figure 16. Reverse Bias Switching Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable

operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 15 is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown in Figure 15 may be found at any case temperature by using the appropriate curve on Figure 17. $T_{J(pk)}$ may be calculated from the data in Figure 20. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base-to-emitter junction reverse-biased. The safe level is specified as a reverse-biased safe operating area (Figure 16). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

MJE18006G

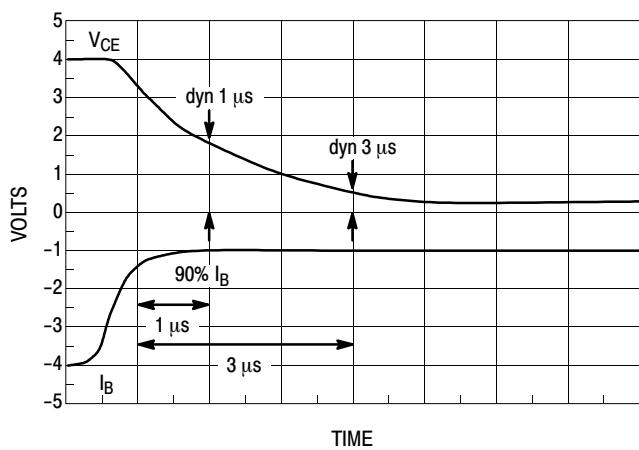


Figure 18. Dynamic Saturation Voltage Measurements

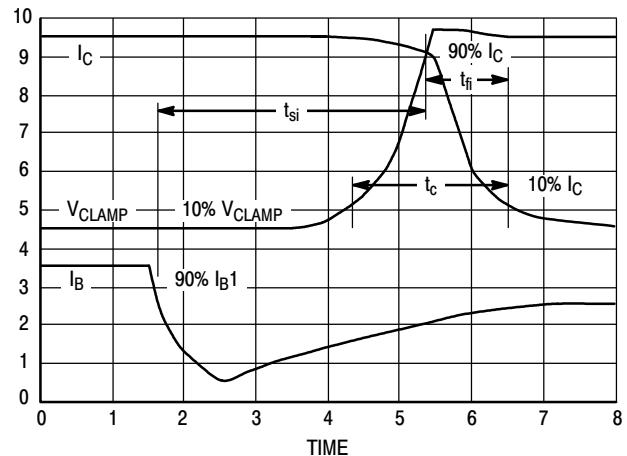
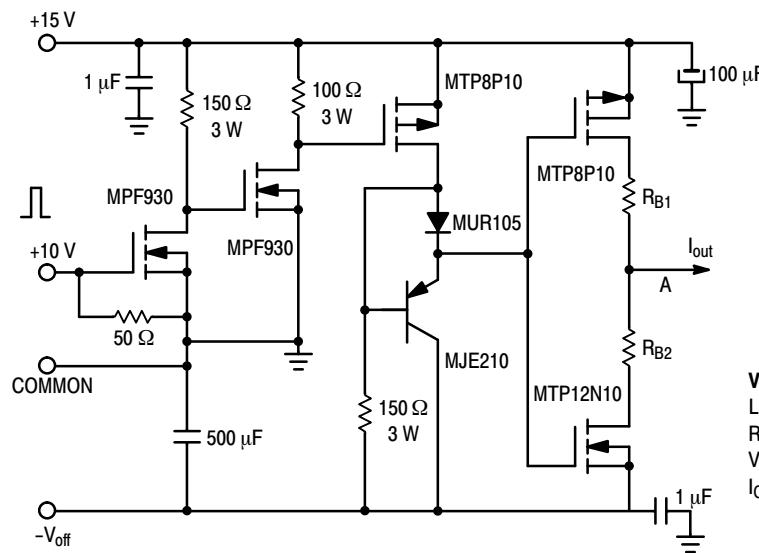


Figure 19. Inductive Switching Measurements



V(BR)CEO(sus)	INDUCTIVE SWITCHING	RBSOA
L = 10 mH	L = 200 μH	L = 500 μH
RB2 = ∞	RB2 = 0	RB2 = 0
V _{CC} = 20 VOLTS	V _{CC} = 15 VOLTS	V _{CC} = 15 VOLTS
I _{C(pk)} = 100 mA	RB1 SELECTED FOR DESIRED I _{B1}	RB1 SELECTED FOR DESIRED I _{B1}

Table 1. Inductive Load Switching Drive Circuit

TYPICAL THERMAL RESPONSE

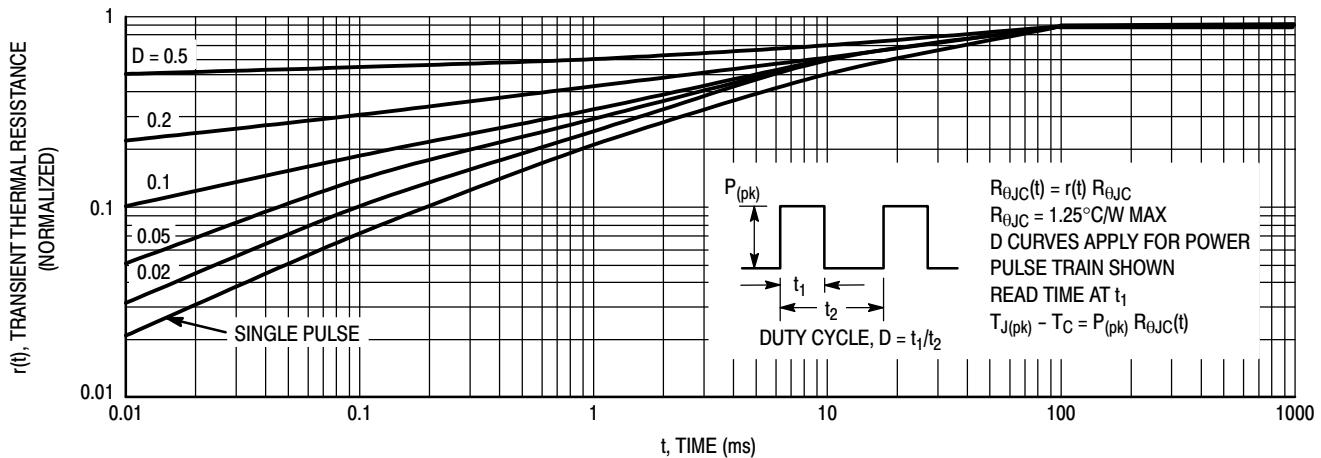


Figure 20. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18006

MECHANICAL CASE OUTLINE

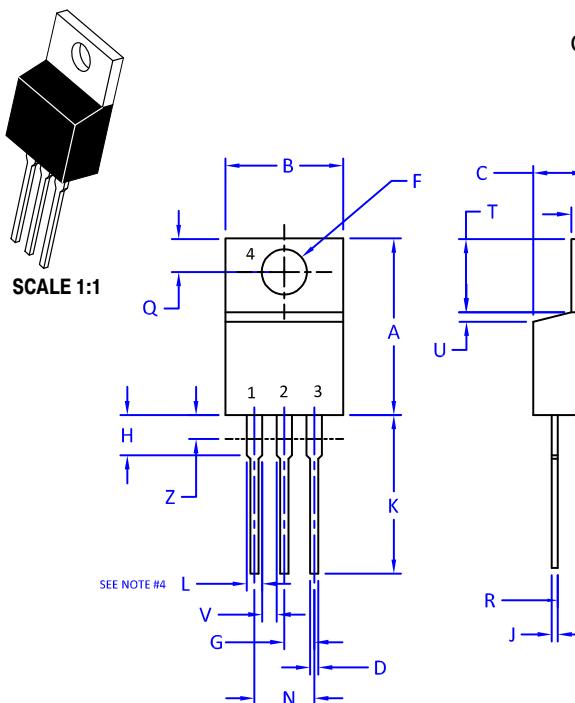
PACKAGE DIMENSIONS

ON Semiconductor®



TO-220 CASE 221A-09 ISSUE AJ

DATE 05 NOV 2019



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	----	1.15	---
Z	----	0.080	---	2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. Emitter
4. COLLECTOR

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. Emitter
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. Emitter
3. COLLECTOR
4. Emitter

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

DOCUMENT NUMBER:	98ASB42148B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TO-220	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative